

High Temperature Silicon Carbide Power Schottky Diode

V_{RRM}	=	1200 V
I_F ($T_C=25^\circ\text{C}$)	=	30 A
Q_C	=	58 nC

Features

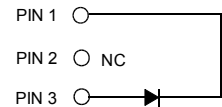
- 1200 V Schottky rectifier
- 250 °C maximum operating temperature
- Electrically isolated base-plate
- Zero reverse recovery charge
- Superior surge current capability
- Positive temperature coefficient of V_F
- Temperature independent switching behavior
- Lowest figure of merit Q_C/I_F
- Available screened to Mil-PRF-19500

Advantages

- High temperature operation
- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Industry's lowest reverse recovery charge
- Industry's lowest device capacitance
- Ideal for output switching of power supplies
- Best in class reverse leakage current at operating temperature

Package

- RoHS Compliant



TO – 257 (Isolated Base-plate Hermetic Package)

Applications

- Down Hole Oil Drilling, Geothermal Instrumentation
- High Temperature DC/DC Converters
- High Temperature Motor and Servo Drives
- High Temperature Inverters
- High Temperature Actuator Control
- Military Power Supplies

Maximum Ratings at $T_j = 250^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values		Unit
			min.	typ.	
Repetitive peak reverse voltage	V_{RRM}			1200	V
Continuous forward current	I_F	$T_C = 25^\circ\text{C}$		30	A
Continuous forward current	I_F	$T_C \leq 225^\circ\text{C}$		9.4	A
RMS forward current	$I_{F(RMS)}$	$T_C \leq 225^\circ\text{C}$		16	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ ms}$		65	A
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}$, $t_p = 10\ \mu\text{s}$		280	A
I^2t value	$\int I^2 dt$	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ ms}$		20	A^2S
Power dissipation	P_{tot}	$T_C = 25^\circ\text{C}$		230	W
Operating and storage temperature	T_j, T_{stg}			-55 to 250	$^\circ\text{C}$

Electrical Characteristics at $T_j = 250^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode forward voltage	V_F	$I_F = 10\text{ A}$, $T_j = 25^\circ\text{C}$		1.6		V
		$I_F = 10\text{ A}$, $T_j = 210^\circ\text{C}$		2.3		
Reverse current	I_R	$V_R = 1200\text{ V}$, $T_j = 25^\circ\text{C}$		1	20	μA
		$V_R = 1200\text{ V}$, $T_j = 250^\circ\text{C}$		55	300	
Total capacitive charge	Q_C	$I_F \leq I_{F,MAX}$ $dI_F/dt = 200\text{ A}/\mu\text{s}$ $T_j = 210^\circ\text{C}$	$V_R = 400\text{ V}$	58		nC
	$V_R = 960\text{ V}$		95			
Switching time	t_s	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$, $T_j = 25^\circ\text{C}$	$V_R = 400\text{ V}$	< 49		ns
			$V_R = 960\text{ V}$			
Total capacitance	C	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$, $T_j = 25^\circ\text{C}$		884		pF
		$V_R = 400\text{ V}$, $f = 1\text{ MHz}$, $T_j = 25^\circ\text{C}$		79		
		$V_R = 1000\text{ V}$, $f = 1\text{ MHz}$, $T_j = 25^\circ\text{C}$		63		

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	1.08	$^\circ\text{C}/\text{W}$
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Mechanical Properties

Mounting torque	M	0.6	Nm
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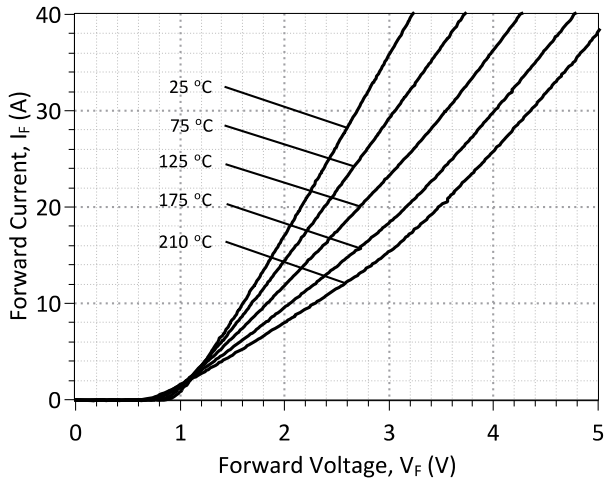


Figure 1: Typical Forward Characteristics

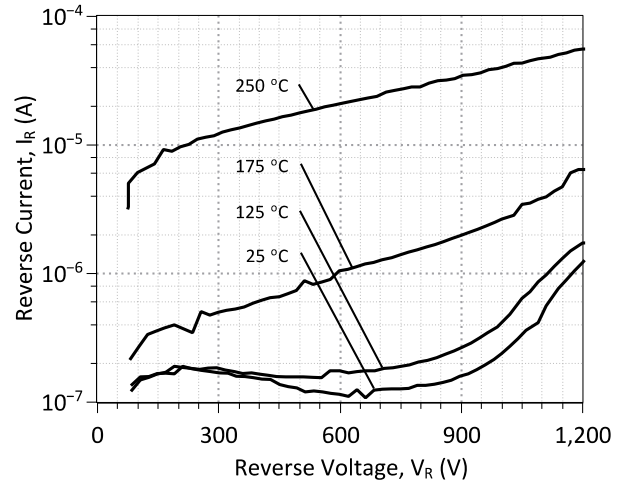


Figure 2: Typical Reverse Characteristics

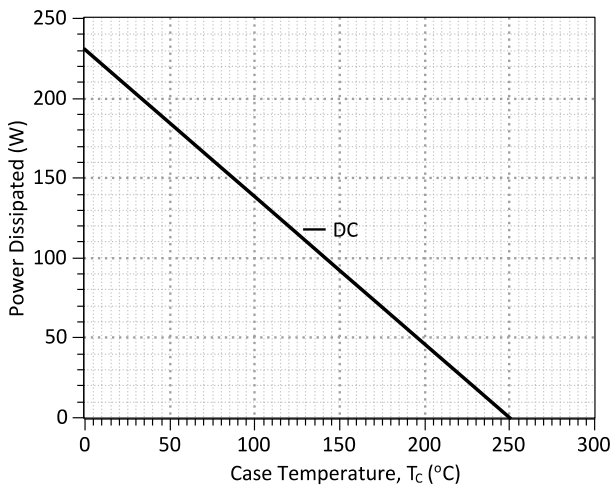
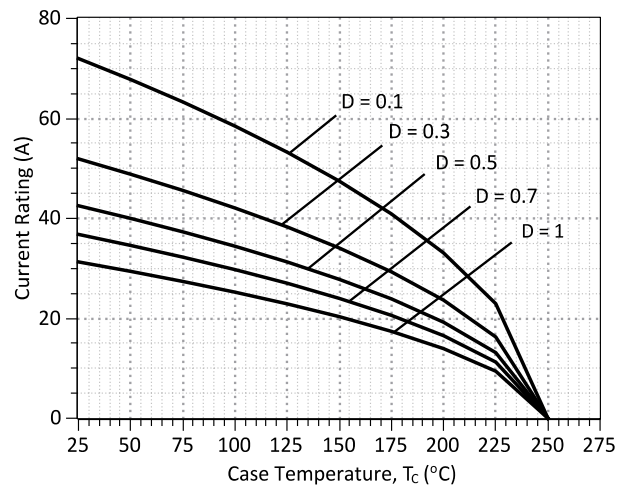


Figure 3: Power Derating Curve



**Figure 4: Current Derating Curves (D = t_p/T , $t_p = 400 \mu s$)
(Considering worst case Z_{th} conditions)**

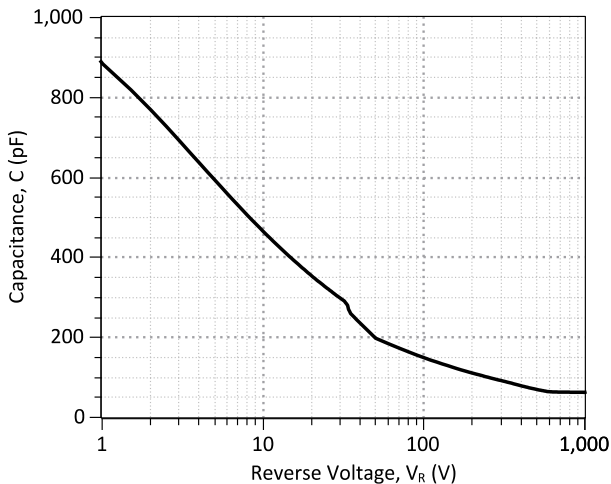


Figure 5: Typical Junction Capacitance vs Reverse Voltage Characteristics

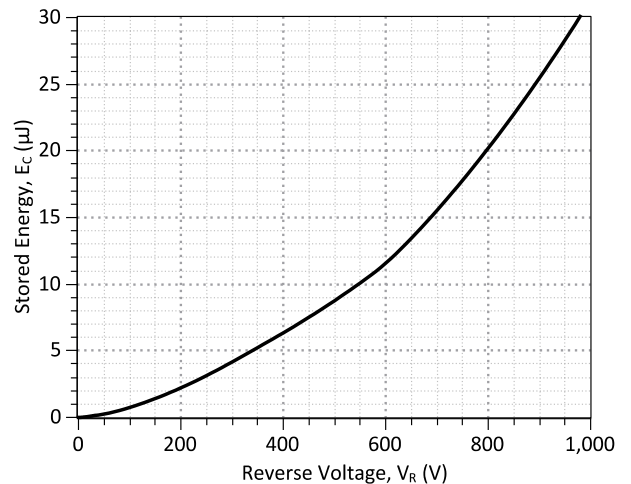


Figure 6: Typical Switching Energy vs Reverse Voltage Characteristics

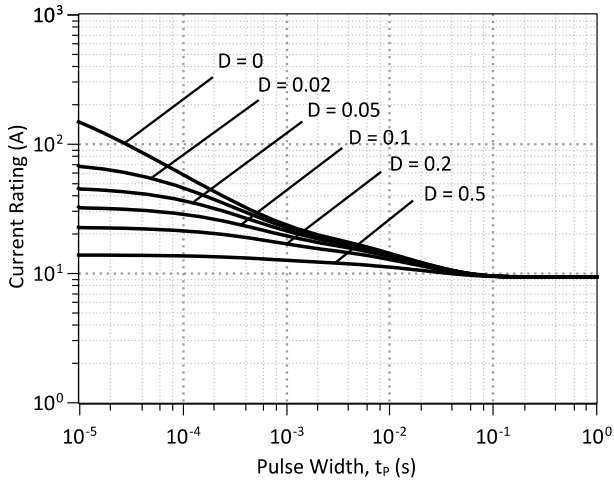


Figure 7: Current vs Pulse Duration Curves at $T_c = 225\text{ }^\circ\text{C}$

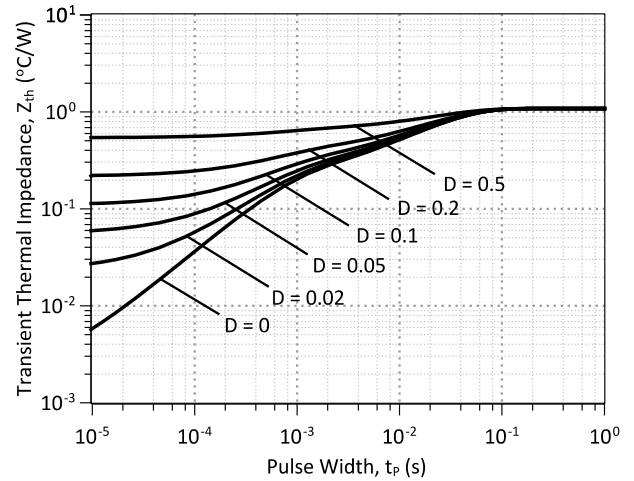
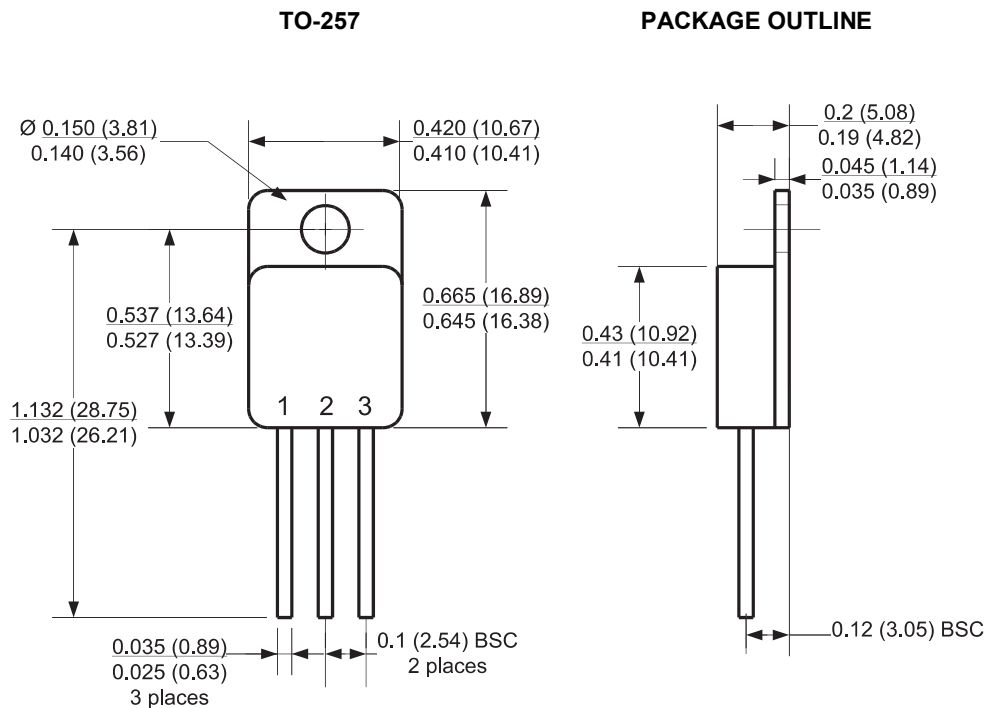


Figure 8: Transient Thermal Impedance

Package Dimensions:



NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

Revision History

Date	Revision	Comments	Supersedes
2014/08/26	1	Updated Electrical Characteristics	
2012/04/24	0	Initial release	

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SPICE Model Parameters

This is a secure document. Copy this code from the SPICE model PDF file on our website into a SPICE software program for simulation of the 1N8028-GA.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      05-SEP-2013   $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
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*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of 1N8028-GA SPICE Model
*
.SUBCKT 1N8028 ANODE KATHODE
D1 ANODE KATHODE 1N8028_25C; Call the Schottky Diode Model
D2 ANODE KATHODE 1N8028_PIN; Call the PiN Diode Model
.MODEL 1N8028_25C D
+ IS      1.74E-13      RS      0.05105
+ TRS1    0.005        TRS2    1.68E-5
+ N       1.2637323    IKF     1.884319
+ EG      1.2          XTI     3
+ CJO     1.15E-09    VJ      0.44
+ M       1.5          FC      0.5
+ TT      1.00E-10    BV      1200
+ IBV     1.00E-03    VPK     1200
+ IAVE    20          TYPE    SiC_Schottky
+ MFG     GeneSiC_Semiconductor
.MODEL 1N8028_PIN D
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+ N       3.1605      IKF     0.00055844
+ EG      3.23        XTI     3
+ FC      0.5         TT      0
+ BV      1200        IBV     1.00E-03
+ VPK     1200        IAVE    20
+ TYPE    SiC_PiN
.ENDS
*
*      End of 1N8028-GA SPICE Model
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